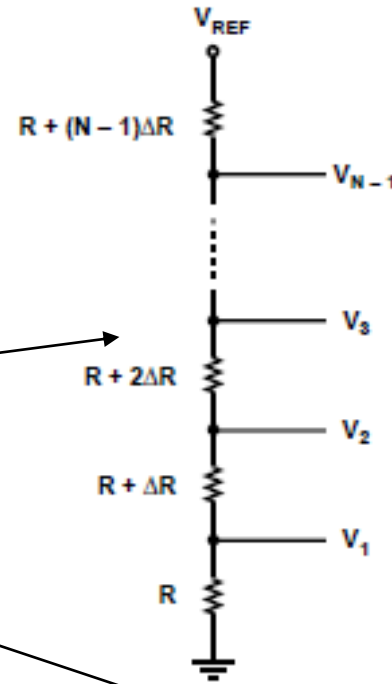


Matching in Analog Integrated Circuits

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In Analog Design Ratios are more important than the Absolute Values

- Absolute values depend on large parameter drifts. Ratios depend on local variation of parameters.
- Specs of Analog/RF Circuits rely critically on Ratios
 - Cap/Res:
 - INL, DNL in DACs
 - MOS:
 - CMRR, PSRR of opamps
 - Gain error in amplifiers
 - I/Q mismatch in RF Rx



$$INL_j(\max) = INL_{N/2} = \frac{N}{8} \left(\frac{\Delta R}{R} \right) V_{REF}$$

$$DNL(\max) \equiv \left(\frac{\Delta R}{2R} \right) V_{REF}$$

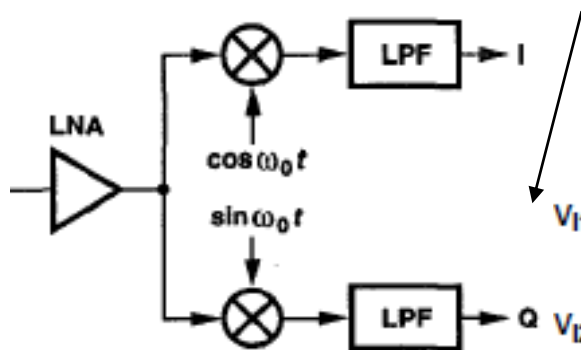
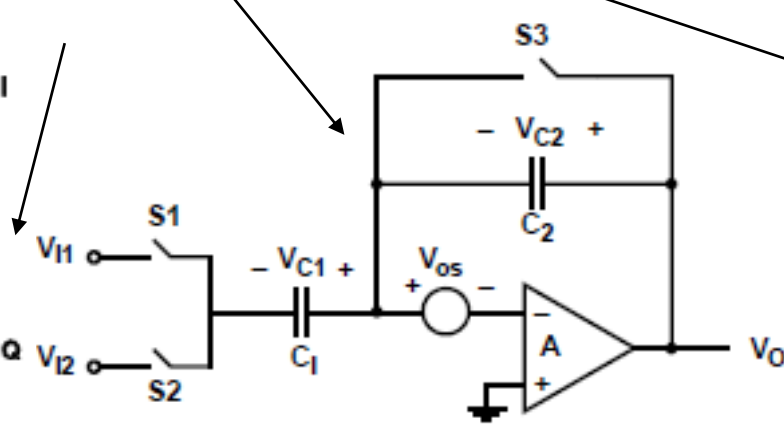
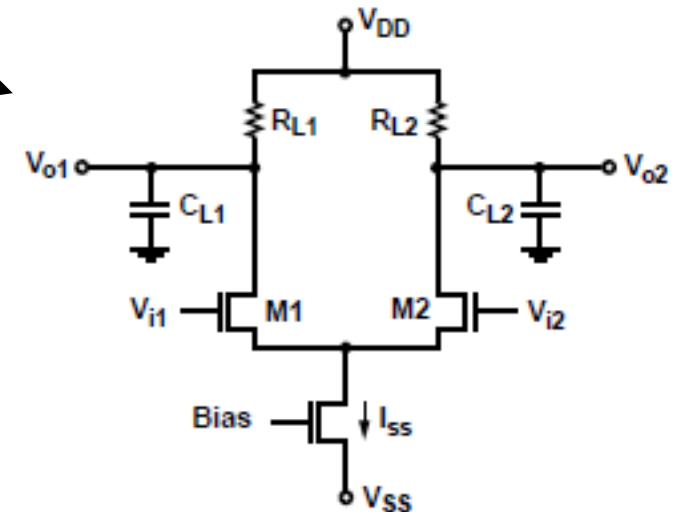


Fig. 2. Direct-conversion receiver.



$$V_O = \left(\frac{C_1}{C_2} \right) (V_{i1} - V_{i2}) + V_{os}$$



Device Matching

- Capacitor

$$C = \frac{\epsilon_0 \epsilon_r}{t_{ox}} WL \quad \left(\frac{\Delta C}{C} \right)^2 = \left(\frac{\Delta \epsilon_r}{\epsilon_r} \right)^2 + \left(\frac{\Delta t_{ox}}{t_{ox}} \right)^2 + \left(\frac{\Delta L}{L} \right)^2 + \left(\frac{\Delta W}{W} \right)^2$$

- Resistor

- $L \gg W$

$$R = \frac{L}{W} R_{\square} = \frac{L}{W} \cdot \frac{\bar{\rho}}{x_j} \quad \left(\frac{\Delta R}{R} \right)^2 = \left(\frac{\Delta L}{L} \right)^2 + \left(\frac{\Delta W}{W} \right)^2 + \left(\frac{\Delta \bar{\rho}}{\bar{\rho}} \right)^2 + \left(\frac{\Delta x_j}{x_j} \right)^2$$

- Caps match better than Resistors

$$\left(\frac{\Delta \epsilon_r}{\epsilon_r} \right) \ll \left(\frac{\Delta \bar{\rho}}{\bar{\rho}} \right) \quad \left(\frac{\Delta W}{W} \right)_{cap} < \left(\frac{\Delta W}{W} \right)_{res} \quad \left(\frac{\Delta t_{ox}}{t_{ox}} \right) < \left(\frac{\Delta x_j}{x_j} \right)$$

- Transistors (Pelgrome JSSC oct.1989)

$$\frac{\sigma^2(\beta)}{\beta^2} = \frac{A_{\beta}^2}{WL} + S_{\beta}^2 D^2 \quad \sigma^2(V_T) = \frac{A_{V_T}^2}{WL} + S_{V_T}^2 D^2$$

A_{β} , A_{V_T} , S_{β} , S_{V_T} are tech constants, D is the separation between the devices.

Accuracy \leftrightarrow Speed Tradeoff

- As W & L are increased, two effects happen:
 - The individual contributions for mismatch i.e. $(\Delta W/W)$ & $(\Delta L/L)$ decrease
 - Actual variation of parameters i.e. ΔW , ΔL also decrease due to more spatial averaging.
 - This happens till the large distance effects kick in.
- Hence, mismatch of the devices decreases as they are made bigger.
- However, speed decreases as devices get bigger. This points to a fundamental trade-off between Accuracy \leftrightarrow Speed.

Symmetry and Matching

- Interdigitized (common centroid) layout
 - Assume that the gradient of variation is described as; $y = mx + b$
 - A (composed of A1 & A2) should be twice of B.

- For layout (a) we have:

$$A1 = mx_1 + b$$

$$A2 = mx_2 + b$$

$$B = mx_3 + b$$

$$\frac{A1 + A2}{B} = \frac{m(x_1 + x_2) + 2b}{mx_3 + b} \neq 2$$

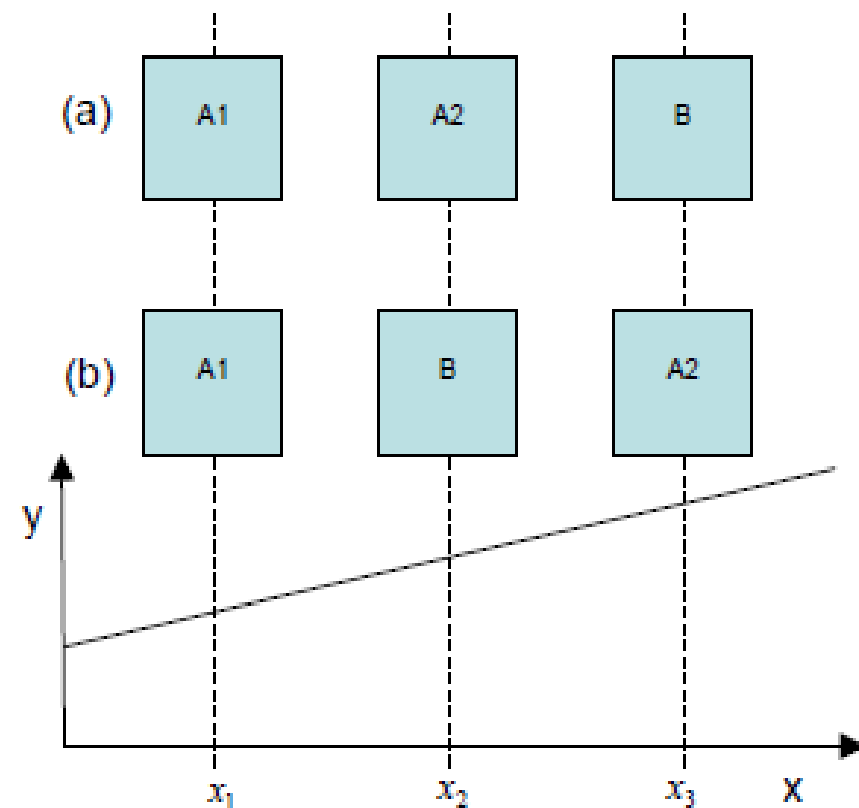
- For layout (b) we have:

$$A1 = mx_1 + b$$

$$A2 = mx_3 + b$$

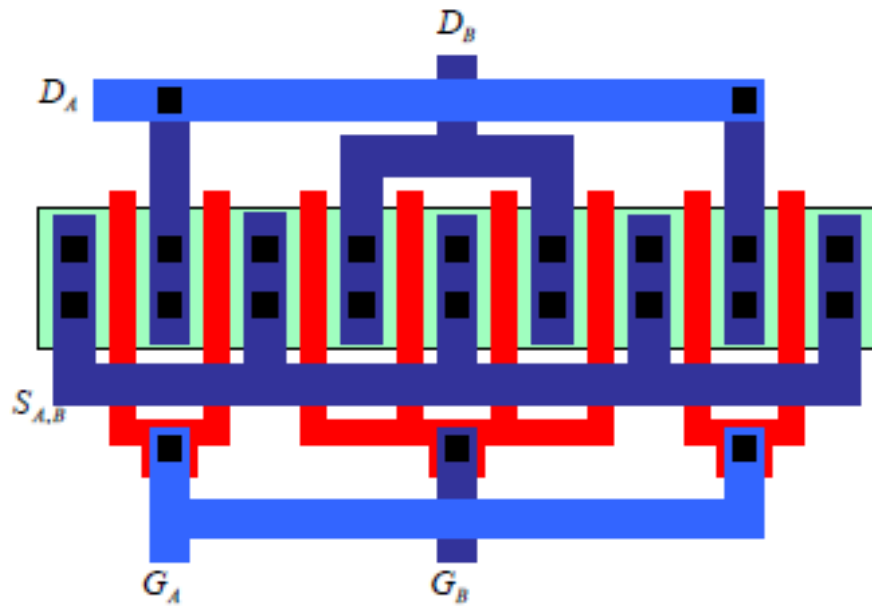
$$B = mx_2 + b$$

$$\frac{A1 + A2}{B} = \frac{m(x_1 + x_3) + 2b}{mx_2 + b} = 2$$

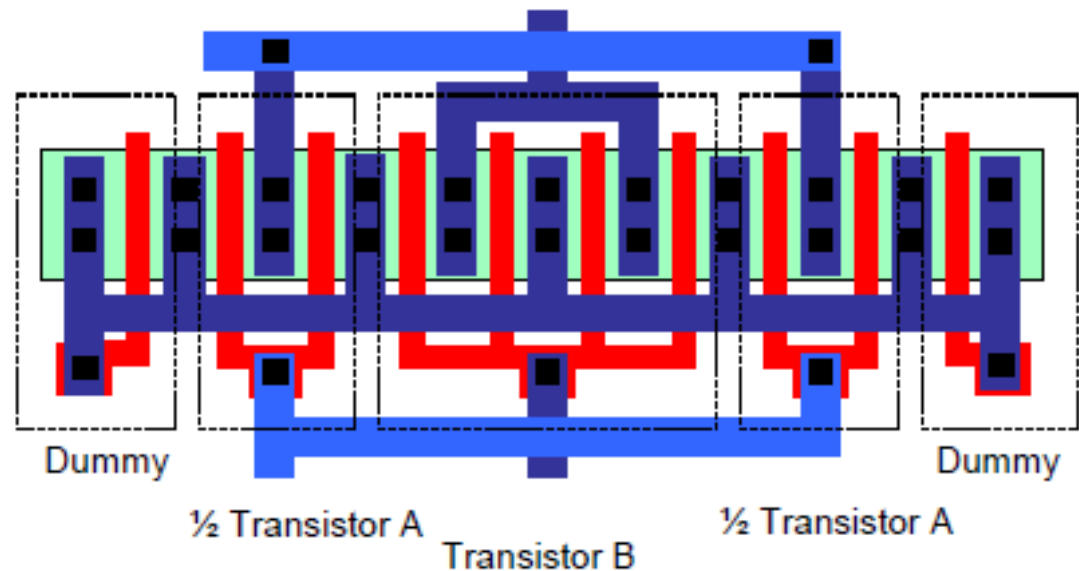


Symmetry and Matching

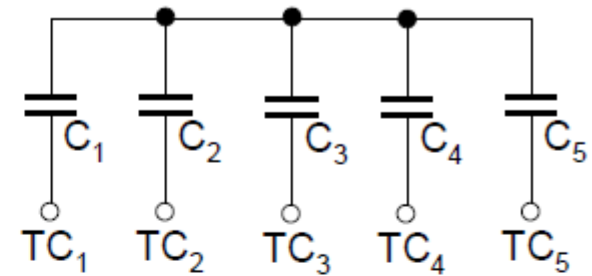
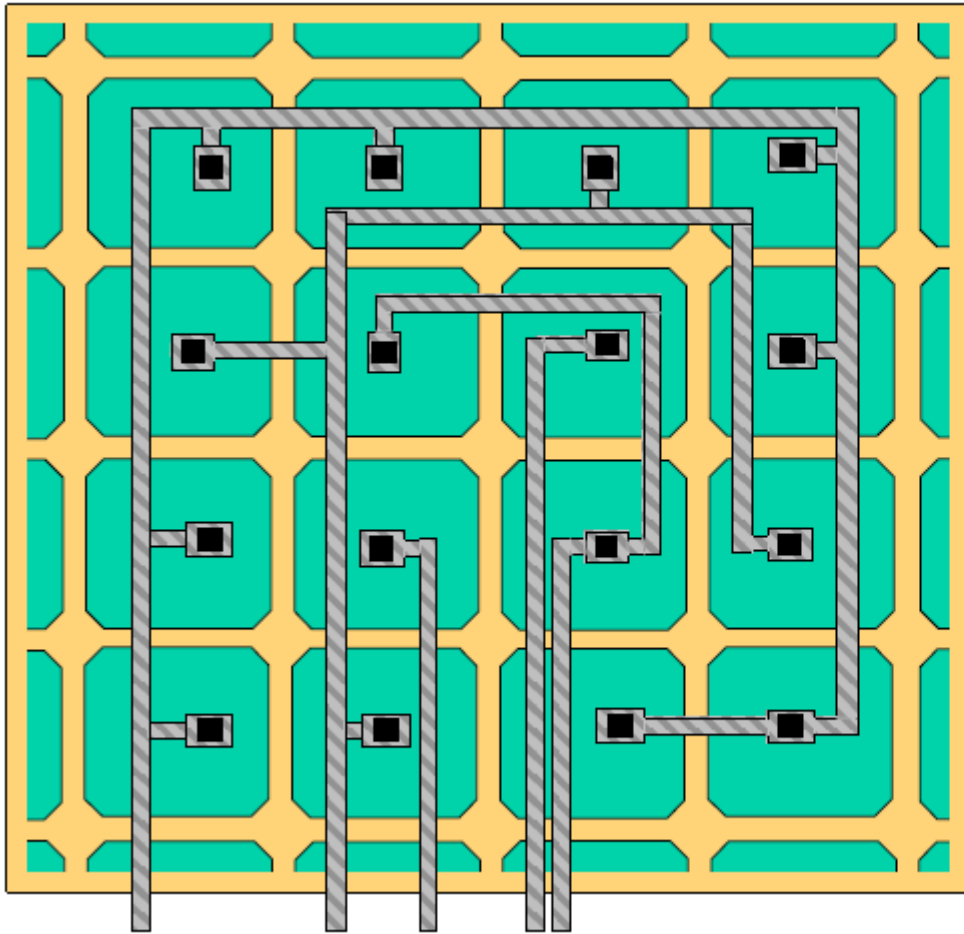
- Dummy transistors improves the matching between transistor A and B by providing similar environment to the circuit that is on the boundary of a layout.



An Example of common centroid layout

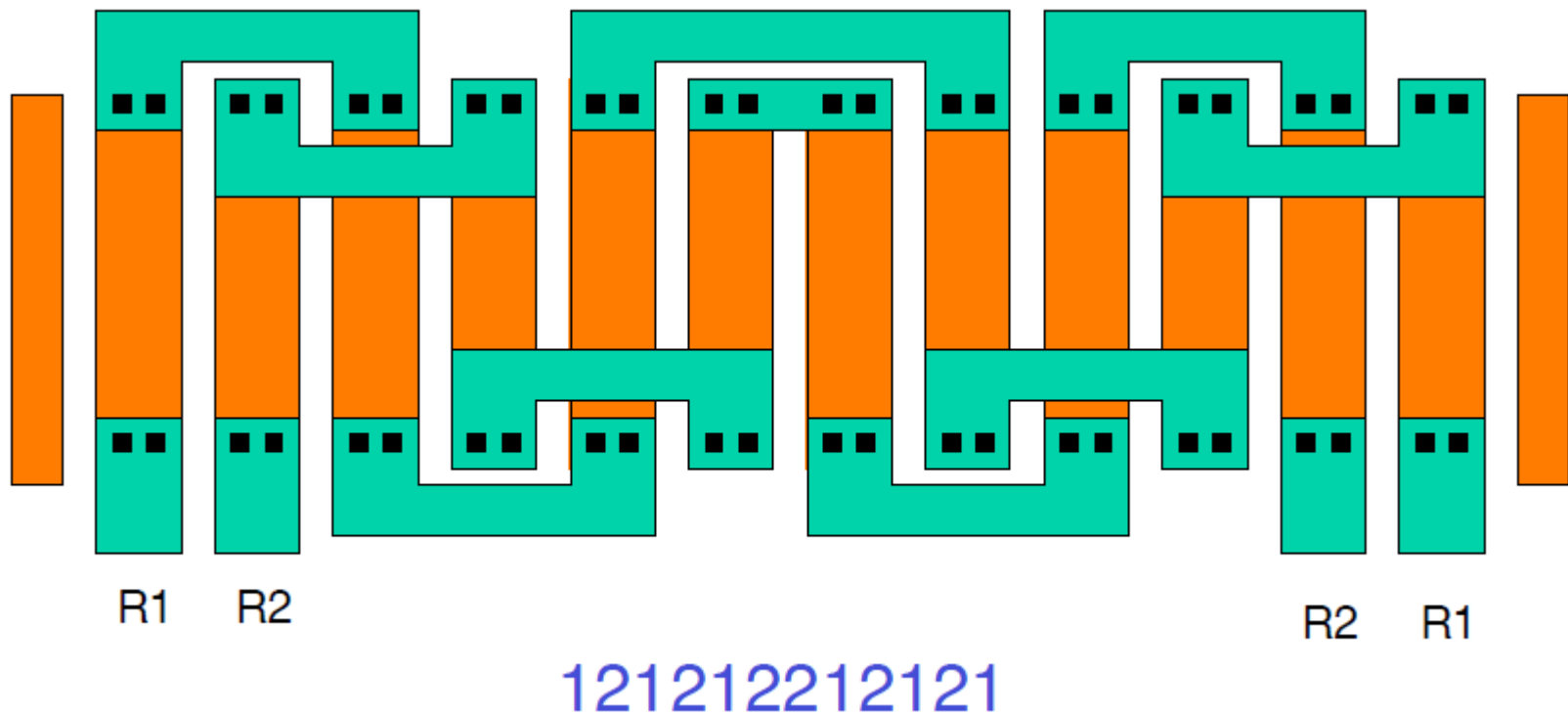


Capacitor Layout



$$\begin{aligned} C_2 &= C_1 \\ C_3 &= 2C_1 \\ C_4 &= 4C_1 \\ C_5 &= 8C_1 \end{aligned}$$

Resistor Layout



Conclusions

- Matching is very critical for Analog IC designs.
- Good layout techniques help in improving matching.
- However, as the feature size decreases, the variation is increasing.
- Designers are resorting to various techniques to manage the growing mismatches.
 - Auto-Zeroing in Comparators.
 - Digital Calibration for mismatch correction.
 - Dynamic Element Matching to randomize or shape the mismatch errors.